

Laser Heating of a Silicon Wafer

A silicon wafer is heated up by a laser that moves radially in and out over time while the wafer itself rotates on its stage. Modeling the incident heat flux from the laser as a spatially distributed heat source on the surface, the transient thermal response of the wafer is obtained. The peak, average, and minimum temperatures during the heating process are computed, as well as the temperature variations across the wafer.

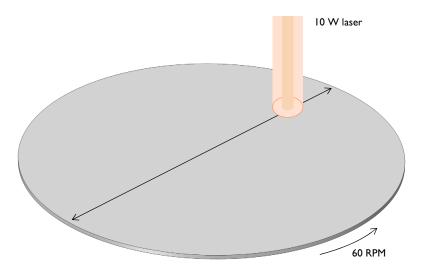


Figure 1: A silicon wafer is heated with a laser that moves back and forth. The wafer is also being rotated about its axis.

Model Definition

A 2-inch silicon wafer, as shown in Figure 1, is heated for one minute by a 10 W laser that moves radially inwards and outwards, while the wafer rotates on its stage. Assuming good thermal isolation from the environment, the only source of heat loss is from the top surface via radiation to the processing chamber walls, which are assumed to be at a fixed temperature of 20 °C.

The laser beam is modeled as a heat source in the plane with Gaussian profile. To set up the heating profile the model uses the built-in Gaussian Pulse functions, which enforce that the integral under the curve equals unity. The focal point is moved by using a

triangular waveform to define its position along the x-axis over time. The wafer is assigned a bulk rotational velocity in the governing heat transfer equation.

The emissivity of the surface of the wafer is approximately 0.8. At the operating wavelength of the laser, it is assumed that absorptivity equals emissivity. The heat load due to the laser is thus multiplied by the emissivity. Assuming also that the laser is operating at a wavelength at which the wafer is opaque, no light is passing through the wafer. Therefore, all of the laser heat is deposited at the surface.

The wafer is meshed using a triangular swept mesh. Swept meshing allows for only a single thin element through the thickness, and still maintains reasonable element size in the plane. A finer mesh would give slightly more accurate predictions of the peak temperature, but predictions of average and minimum temperature would not be greatly affected.

Results and Discussion

Figure 2 plots the maximum, minimum, and average temperatures of the wafer, while Figure 3 shows the difference between the maximum and minimum temperature. The temperature distribution across the wafer is plotted in Figure 4.

The heating profile does introduce some significant temperature variations, because the laser deposits the same amount of heat over a larger total swept area when it is focused at the outside of the wafer. An interesting modification to this example would be to investigate alternative heating profiles for smoother heating.

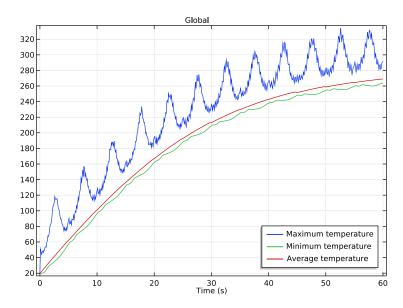


Figure 2: Maximum, minimum, and average temperatures of the wafer as functions of time.

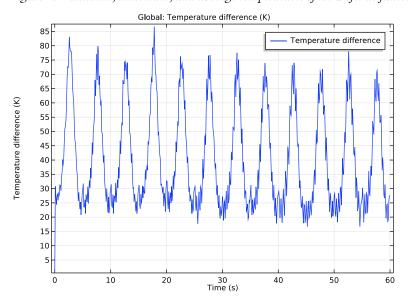


Figure 3: Difference between maximum and minimum temperatures on the wafer.

Time=60 s Surface: Temperature (K) Arrow Surface: Velocity field

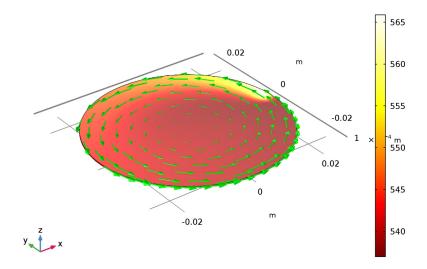


Figure 4: Temperature variation across the wafer. The arrow plot describes the velocity of the wafer.

Application Library path: COMSOL_Multiphysics/Heat_Transfer/ laser_heating_wafer

Modeling Instructions

From the File menu, choose New.

NEW

In the New window, click Model Wizard.

MODEL WIZARD

- I In the Model Wizard window, click 3D.
- 2 In the Select Physics tree, select Heat Transfer>Heat Transfer in Solids (ht).
- 3 Click Add.

- 4 Click Study.
- 5 In the Select Study tree, select Preset Studies>Time Dependent.
- 6 Click Done.

GLOBAL DEFINITIONS

Start by defining parameters for use in the geometry, functions, and physics settings.

Parameters

- I On the Home toolbar, click Parameters.
- 2 In the Settings window for Parameters, locate the Parameters section.
- **3** In the table, enter the following settings:

Name	Expression	Value	Description
r_wafer	1[in]	0.0254 m	Wafer radius
thickness	275[um]	2.75E-4 m	Wafer thickness
v_rotation	60[rpm]	I I/s	Rotational speed
angular_v	2*pi*v_rotation	6.283 1/s	Angular velocity
period	10[s]	10 s	Time for laser to move back and forth
r_spot	2[mm]	0.002 m	Laser beam radius
emissivity	0.8	0.8	Surface emissivity of wafer
p_laser	10[W]	10 W	Laser power

Here, the unit 'rpm' is revolution per minute.

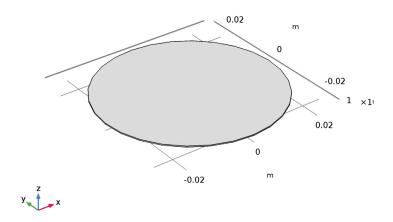
GEOMETRY I

Create a cylinder for the silicon wafer.

Cylinder I (cyll)

- I On the Geometry toolbar, click Cylinder.
- 2 In the Settings window for Cylinder, locate the Size and Shape section.
- 3 In the Radius text field, type r_wafer.
- 4 In the Height text field, type thickness.

5 Click **Build All Objects**.



DEFINITIONS

Define functions for use before setting up the physics.

Variables 1

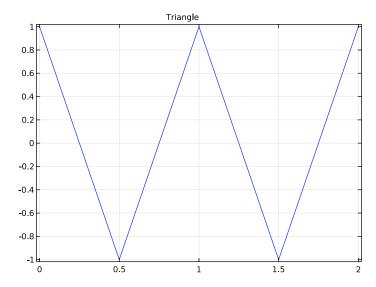
- I In the Model Builder window, under Component I (compl) right-click Definitions and choose Variables.
- 2 In the Settings window for Variables, locate the Variables section.
- **3** In the table, enter the following settings:

Name	Expression	Unit	Description
x_focus	r_wafer*Triangle(t/ period)	m	x-location of laser focal point
y_focus	O[m]	m	<pre>y_location of laser focal point</pre>
r_focus	sqrt((x-x_focus)^2+(y- y_focus)^2)	m	distance from focal point
Flux	((2*p_laser)/(pi* r_spot^2))*exp(-(2* r_focus^2)/r_spot^2)	W/m²	laser heat flux, Gaussian profile

Waveform I (wvI)

I On the Home toolbar, click Functions and choose Local>Waveform.

- 2 In the Settings window for Waveform, type Triangle in the Function name text field.
- 3 Locate the Parameters section. From the Type list, choose Triangle.
- 4 Clear the **Smoothing** check box.
- 5 In the Angular frequency text field, type 2*pi.
- 6 In the Phase text field, type pi/2.
- 7 In the Amplitude text field, type 1.
- 8 Click Plot.



Average I (aveop1)

- 1 On the **Definitions** toolbar, click **Component Couplings** and choose **Average**.
- 2 Click in the **Graphics** window and then press Ctrl+A to select all domains.

Maximum I (maxop I)

- I On the Definitions toolbar, click Component Couplings and choose Maximum.
- 2 Click in the **Graphics** window and then press Ctrl+A to select all domains.

Minimum I (minopl)

- I On the **Definitions** toolbar, click **Component Couplings** and choose **Minimum**.
- 2 Click in the **Graphics** window and then press Ctrl+A to select all domains.

HEAT TRANSFER IN SOLIDS (HT)

Set up the physics. First, include the wafer's rotational velocity in the governing heat transfer equation.

Solid 1

In the Model Builder window, under Component I (compl)>Heat Transfer in Solids (ht) click Solid I.

Translational Motion I

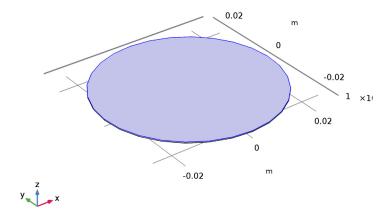
- I On the Physics toolbar, click Attributes and choose Translational Motion.
- 2 In the Settings window for Translational Motion, locate the Translational Motion section.
- **3** Specify the \mathbf{u}_{trans} vector as

-y*angular_v	x
x*angular_v	у
0	z

Next, add heat flux and surface-to-ambient radiation on the wafer's top surface.

Heat Flux I

- I On the Physics toolbar, click Boundaries and choose Heat Flux.
- 2 Select Boundary 4 only.



3 In the Settings window for Heat Flux, locate the Heat Flux section.

4 In the q_0 text field, type emissivity*Flux.

Diffuse Surface 1

- I On the Physics toolbar, click Boundaries and choose Diffuse Surface.
- 2 Select Boundary 4 only.
- 3 In the Settings window for Diffuse Surface, locate the Surface Emissivity section.
- **4** From the ε list, choose **User defined**. In the associated text field, type emissivity.

ADD MATERIAL

- I On the Home toolbar, click Add Material to open the Add Material window.
- 2 Go to the Add Material window.
- 3 In the tree, select Built-In>Silicon.
- 4 Click Add to Component in the window toolbar.
- 5 On the Home toolbar, click Add Material to close the Add Material window.

MESH I

Use a fine triangular swept mesh.

Swept I

- I In the Model Builder window, under Component I (compl) right-click Mesh I and choose Swept.
- 2 In the Settings window for Swept, click to expand the Sweep method section.
- 3 Locate the Sweep Method section. From the Face meshing method list, choose Triangular (generate prisms).

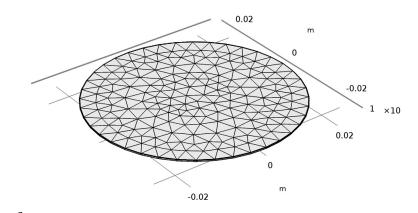
Distribution I

- I Right-click Component I (compl)>Mesh I>Swept I and choose Distribution.
- 2 In the Settings window for Distribution, locate the Distribution section.
- 3 In the Number of elements text field, type 1.

Size

- I In the Model Builder window, under Component I (compl)>Mesh I click Size.
- 2 In the Settings window for Size, locate the Element Size section.
- **3** From the **Predefined** list, choose **Fine**.

4 Click Build All.



STUDY I

Step 1: Time Dependent

- I In the Settings window for Time Dependent, locate the Study Settings section.
- 2 In the Times text field, type range (0,0.1,60).
- 3 On the Home toolbar, click Compute.

RESULTS

Temperature (ht)

The first default plot shows the temperature on the wafer surface. Add an arrow plot for the velocity field describing the wafer rotation.

Arrow Surface I

- I In the Model Builder window, under Results right-click Temperature (ht) and choose Arrow Surface.
- 2 In the Settings window for Arrow Surface, click Replace Expression in the upper-right corner of the Expression section. From the menu, choose Model>Component I> Heat Transfer in Solids>ht.ux,ht.uy,ht.uz Velocity field.

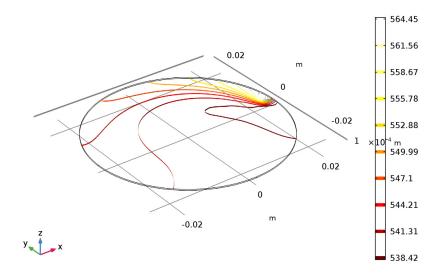
- 3 Locate the Coloring and Style section. Select the Scale factor check box.
- 4 In the associated text field, type 0.036.
- 5 From the Color list, choose Green.
- 6 On the Temperature (ht) toolbar, click Plot.
- 7 Click the **Zoom Extents** button on the **Graphics** toolbar.

Compare the temperature variation with that shown in Figure 4.

Isothermal Contours (ht)

The second default plot shows the isosurface temperature.

Time=60 s Isosurface: Temperature (K)



ID Plot Group 3

- I On the Home toolbar, click Add Plot Group and choose ID Plot Group.
- 2 In the Settings window for ID Plot Group, click to expand the Legend section.
- 3 From the Position list, choose Lower right.

Global I

- I Right-click ID Plot Group 3 and choose Global.
- 2 In the Settings window for Global, locate the y-Axis Data section.

3 In the table, enter the following settings:

Expression	Unit	Description
maxop1(T)	degC	Maximum temperature
minop1(T)	degC	Minimum temperature
aveop1(T)	degC	Average temperature

4 On the ID Plot Group 3 toolbar, click Plot.

Compare the plot showing the maximum, minimum and average temperature with Figure 2.

Global I

- I On the Home toolbar, click Add Plot Group and choose ID Plot Group.
- 2 In the Model Builder window, right-click ID Plot Group 4 and choose Global.
- 3 In the Settings window for Global, locate the y-Axis Data section.
- **4** In the table, enter the following settings:

Expression	Unit	Description
maxop1(T)-minop1(T)	K	Temperature difference

5 On the ID Plot Group 4 toolbar, click Plot.

Finish the result analysis by comparing the generated plot with Figure 3.